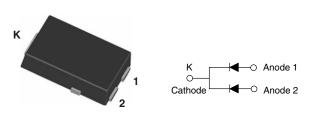
Vishay Semiconductors

Hyperfast Rectifier, 2 x 5 A FRED Pt[®]



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TO-277A (SMPC)

| PRODUCT SUMMARY | | | | | | |
|----------------------------------|----------------|--|--|--|--|--|
| Package | TO-277A (SMPC) | | | | | |
| I _{F(AV)} | 2 x 5 A | | | | | |
| V _R | 200 V | | | | | |
| V _F at I _F | 0.75 V | | | | | |
| t _{rr (typ.)} | 25 ns | | | | | |
| T _J max. | 175 °C | | | | | |
| Diode variation | Dual die | | | | | |

FEATURES

- Hyperfast recovery time, reduced Q_{rr}, and soft recovery
- 175 °C maximum operating junction temperature
- Specified for output and snubber operation
- Low forward voltage drop
- Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- AEC-Q101 qualified, meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see <u>www.vishav.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

State of the art hyperfast recovery rectifiers specifically designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness, and reliability characteristics.

These devices are intended for use in snubber, boost, piezo-injection, as high frequency rectifiers and freewheeling diodes.

The extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element.

| ABSOLUTE MAXIMUM RATINGS | | | | | | |
|---|------------|--|--------------------------|-------------|-------|--|
| PARAMETER | | SYMBOL | TEST CONDITIONS | VALUES | UNITS | |
| Peak repetitive reverse voltage | | V _{RRM} | | 200 | V | |
| Average rectified forward current | per device | I _{F(AV)} | T _{Sp} = 155 °C | 10 | | |
| Average rectilied forward current | per diode | | | 5 | А | |
| Non-repetitive peak surge current | | I _{ESM} T _{.1} = 25 °C | | 130 | ~ | |
| Non-repetitive peak surge current | per diode | IFSM | 1j = 25° C | 70 | | |
| Operating junction and storage temperatures | | T _J , T _{Stg} | | -65 to +175 | °C | |

| ELECTRICAL SPECIFICATIONS (T _J = 25 $^{\circ}$ C unless otherwise specified) | | | | | | |
|--|-------------------------------------|---|------|------|------|-------|
| PARAMETER | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNITS |
| Breakdown voltage, blocking voltage | V _{BR} , V _R | I _R = 100 μA | 200 | - | - | |
| Forward voltage, per diode | VF | I _F = 5 A | - | 0.92 | 0.98 | V |
| i olward voltage, per diode | ۷F | I _F = 5 A, T _J = 150 °C | - | 0.75 | 0.82 | |
| Reverse leakage current, per diode | | $V_{R} = V_{R}$ rated | - | - | 2 | |
| neverse leakage current, per diode | I _R | $T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$ | - | 6 | 80 | μA |
| Junction capacitance | CT | V _R = 200 V | - | 17 | - | pF |

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(e3) RoHS

COMPLIANT HALOGEN



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| DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25$ °C unless otherwise specified) | | | | | | | | |
|---|----------------------|--|--|------|------|-------|-----------|--|
| PARAMETER | SYMBOL | TEST CO | MIN. | TYP. | MAX. | UNITS | | |
| | | | I _F = 1.0 A, dI _F /dt = 50 A/μs, V _R = 30 V | | 25 | - | | |
| Reverse recovery time | + | I _F = 0.5 A, I _R = 1 A, I _{rr} = 0.25 A | | - | - | 25 | ns | |
| Reverse recovery time t _{rr} | ۲r | T _J = 25 °C | | - | 18 | - | - A nC | |
| | | T _J = 125 °C | l _F = 5 A dl _F /dt = 200 A/µs | - | 28 | - | | |
| Pools receivers ourrent | Deale measurement in | T _J = 25 °C | | - | 2 | - | | |
| Peak recovery current I _{RRM} | IRRM | T _J = 125 °C | $V_{\rm B} = 160 {\rm V}$ | - | 3.8 | - | | |
| Reverse recovery charge 0 | 0 | T _J = 25 °C | | - | 18 | - | | |
| | Q _{rr} | T _J = 125 °C | | - | 53 | - | | |

| THERMAL - MECHANICAL SPECIFICATIONS | | | | | | |
|---|-----------------------------------|---------------------------|--------|------|------|-------|
| PARAMETER | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNITS |
| Maximum junction and storage temperature range | T _J , T _{Stg} | | -65 | - | 175 | °C |
| Thermal resistance, junction to solder pad, per diode | R _{thJ-Sp} | | - | 2.5 | 3.5 | °C/W |
| Approvimeto weight | | | | 0.1 | | g |
| Approximate weight | | | 0.0035 | | oz. | |
| Marking device | | Case style TO-277A (SMPC) | | SC | H2 | |

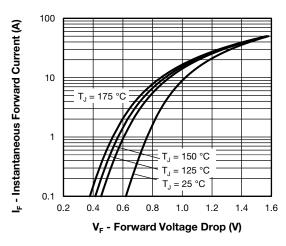


Fig. 1 - Typical Forward Voltage Drop Characteristics

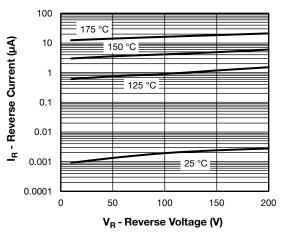
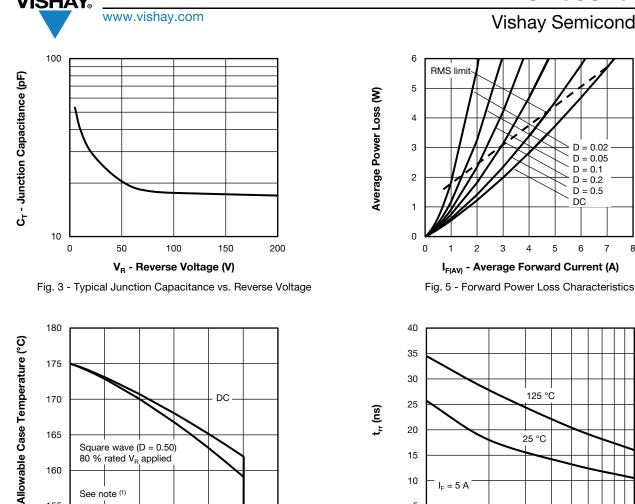


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage



VS-10CSH02HM3

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D = 0.02

D = 0.05 D = 0.1

D = 0.2 D = 0.5 DC

> 8 7

> > 1000

4 5 6

125 °C

25 °C

dl_F/dt (A/µs)

Fig. 6 - Typical Reverse Recovery Time vs. dl_F/dt

10

5

125 °C

25 °C

1000

100

I₅ = 5 A



See note (1)

1

2

3

I_{F(AV)} - Average Forward Current (A)

Fig. 4 - Maximum Allowable Case Temperature

vs. Average Forward Current

4

5

90

70

50

30

10 100

Q_{rr} (nC)

6

 $I_F = 5 A$

155

0

⁽¹⁾ Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$; Pd = Forward power loss = $I_{F(AV)} \times V_{FM}$ at ($I_{F(AV)}/D$) (see fig. 5);

 Pd_{REV} = Inverse power loss = $V_{R1} \times I_R (1 - D)$; I_R at V_{R1} = rated V_R

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Fig. 7 - Typical Stored Charge vs. dl_F/dt

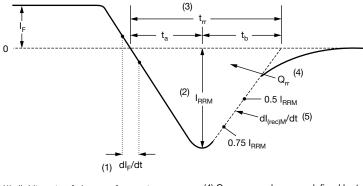
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dl_F/dt (A/µs)

VS-10CSH02HM3

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- (1) dl_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) t_{rr} reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.

(4) ${\rm Q}_{\rm rr}$ - area under curve defined by ${\rm t}_{\rm rr}$ and ${\rm I}_{\rm RRM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) $dI_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 8 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

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| Device code | VS- | 10 | С | s | н | 02 | Н | М3 |
|-------------|------------|------|------------------|----------------------------------|------------------|---------|---------|---------|
| | 1 | 2 | 3 | 4 | 5 | 6 | 7 | 8 |
| | 1 - 2 - | Cur | rent rati | niconduo ng (10 = | = 10 A) | oduct | | |
| | 3 - | | | iguration n catho | | | | |
| | 4 - | | | package | | | | |
| | 5 - | Pro | cess typ | e, | | | | |
| | 6 - 7 - | Volt | age coo AEC-Q | ist recov le (02 = 101 qua | 200 V) lified | | | |
| | 8 - | • M3 | = halog | en-free, | RoHS-0 | complia | nt, and | termina |

| ORDERING INFORMATION (Example) | | | | | | | |
|--------------------------------|-------------------|------------------------|------------------------------------|--|--|--|--|
| PREFERRED P/N | QUANTITY PER REEL | MINIMUM ORDER QUANTITY | PACKAGING DESCRIPTION | | | | |
| VS-10CSH02HM3/86A | 1500 | 1500 | 7" diameter plastic tape and reel | | | | |
| VS-10CSH02HM3/87A | 6500 | 6500 | 13" diameter plastic tape and reel | | | | |

| LINKS TO RELATED DOCUMENTS | | | | | |
|-------------------------------------|--------------------------|--|--|--|--|
| Dimensions www.vishay.com/doc?95570 | | | | | |
| Part marking information | www.vishay.com/doc?95565 | | | | |
| Packaging information | www.vishay.com/doc?88869 | | | | |

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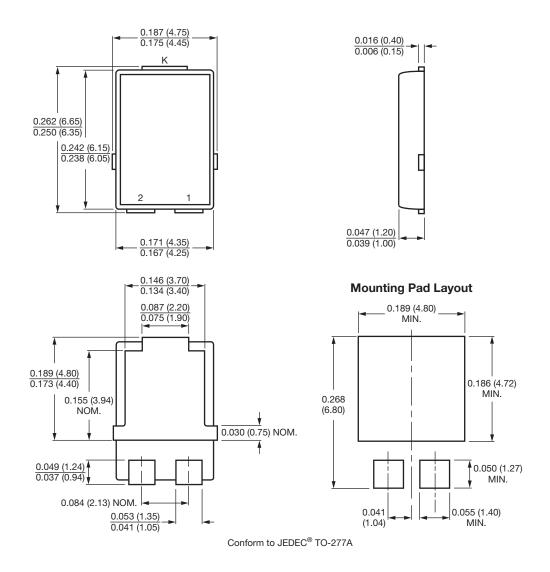
Outline Dimensions





TO-277A (SMPC)

DIMENSIONS in inches (millimeters)





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